

Transistors

●Absolute maximum ratings (Ta=25°C)

Tr1

Parameter	Symbol	Limits	Unit
Collector-base voltage	V _{CB0}	-15	V
Collector-emitter voltage	V _{CEO}	-12	V
Emitter-base voltage	V _{EBO}	-6	V
Collector current	I _C	-3	A
	I _{CP}	-6	A *1
Power dissipation	P _C	500	mW/Total *2
		1.25	W/Total *3
		0.9	W/Element *3
Junction temperature	T _j	150	°C
Range of storage temperature	T _{stg}	-55 to +150	°C

*1 Single pulse, Pw=1ms.

*2 Each terminal mounted on a recommended land.

*3 Mounted on a 25×25×¹0.8mm ceramic substrate.

Tr 2

Parameter	Symbol	Limits	Unit
Collector-base voltage	V _{CB0}	15	V
Collector-emitter voltage	V _{CEO}	12	V
Emitter-base voltage	V _{EBO}	6	V
Collector current	I _C	3	A
	I _{CP}	6	A *1
Power dissipation	P _C	500	mW/Total *2
		1.25	W/Total *3
		0.9	W/Element *3
Junction temperature	T _j	150	°C
Range of storage temperature	T _{stg}	-50 to +150	°C

*1 Single pulse, Pw=1ms.

*2 Each terminal mounted on a recommended land.

*3 Mounted on a 25×25×¹0.8mm ceramic substrate.

●Electrical characteristics (Ta=25°C)

Tr1

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{CB0}	-15	-	-	V	I _C =-10μA
Collector-emitter breakdown voltage	BV _{CEO}	-12	-	-	V	I _C =-1mA
Emitter-base breakdown voltage	BV _{EBO}	-6	-	-	V	I _E =-10μA
Collector cutoff current	I _{CB0}	-	-	-100	nA	V _{CB} =-15V
Emitter cutoff current	I _{EBO}	-	-	-100	nA	V _{EB} =-6V
Collector-emitter saturation voltage	V _{CE(sat)}	-	-120	-250	mV	I _C =-1.5A, I _B =-30mA
DC current gain	h _{FE}	270	-	680	-	V _{CE} =-2V, I _C =-500mA*
Transition frequency	f _T	-	280	-	MHz	V _{CE} =-2V, I _E =500mA, f=100MHz*
Collector output capacitance	C _{ob}	-	30	-	pF	V _{CB} =-10V, I _E =0A, f=1MHz

* Pulsed

Tr 2

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{CB0}	15	-	-	V	I _C =10μA
Collector-emitter breakdown voltage	BV _{CEO}	12	-	-	V	I _C =1mA
Emitter-base breakdown voltage	BV _{EBO}	6	-	-	V	I _E =10μA
Collector cutoff current	I _{CB0}	-	-	100	nA	V _{CB} =15V
Emitter cutoff current	I _{EBO}	-	-	100	nA	V _{EB} =6V
Collector-emitter saturation voltage	V _{CE(sat)}	-	120	250	mV	I _C =1.5A, I _B =30mA
DC current gain	h _{FE}	270	-	680	-	V _{CE} =2V, I _C =500mA*
Transition frequency	f _T	-	360	-	MHz	V _{CE} =2V, I _E =-500mA, f=100MHz*
Collector output capacitance	C _{ob}	-	30	-	pF	V _{CB} =10V, I _E =0A, f=1MHz

* Pulsed

Transistors

●Electrical characteristic curves

Tr1(PNP)

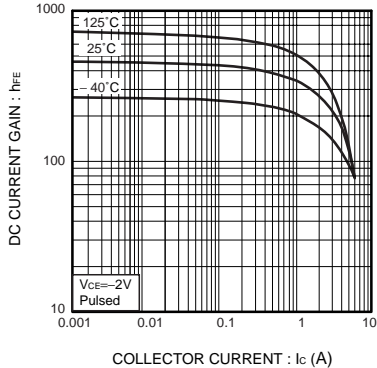


Fig.1. DC current gain vs. collector current

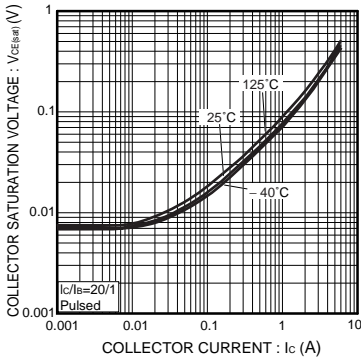


Fig.2. Collector-emitter saturation voltage vs. collector current

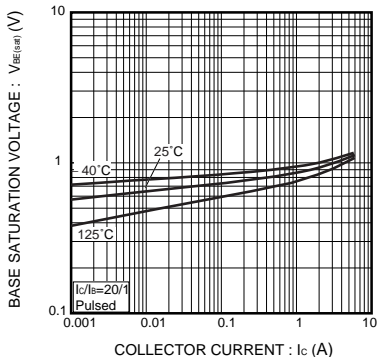


Fig.3. Base-emitter saturation voltage vs. collector current

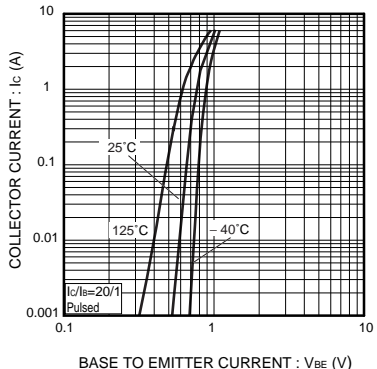


Fig.4. Grounded emitter propagation characteristics

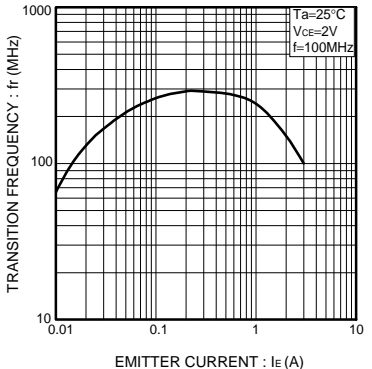


Fig.5. Gain bandwidth product vs. emitter current

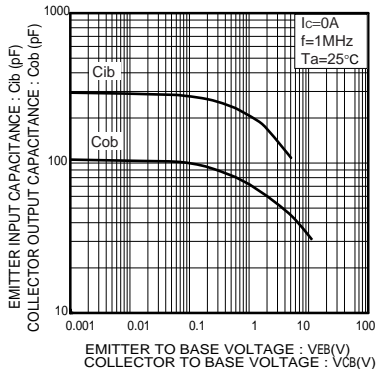


Fig.6. Collector output capacitance vs. collector-base voltage
Emitter input capacitance vs. emitter-base voltage

Tr2(NPN)

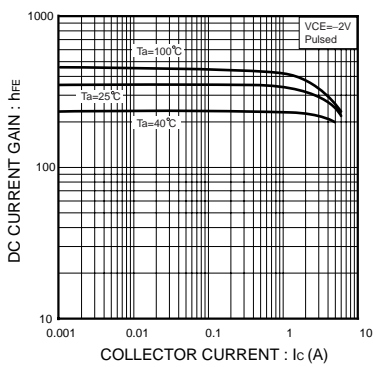


Fig.7. DC current gain vs. collector current

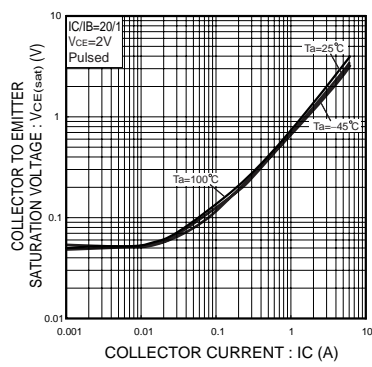


Fig.8. Collector-emitter saturation voltage vs. collector current

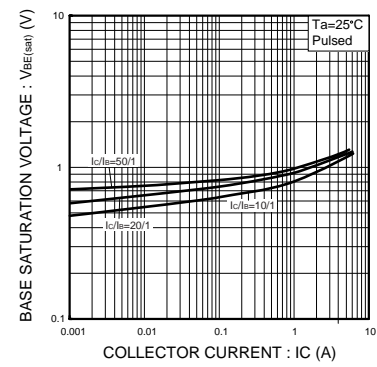


Fig.9. Base-emitter saturation voltage vs. collector current

Transistors

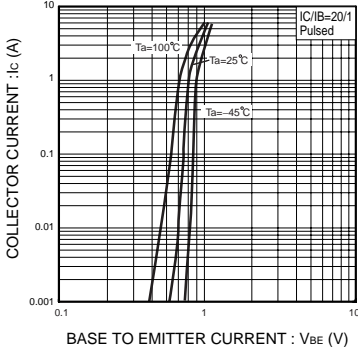


Fig.10 Grounded emitter propagation characteristics

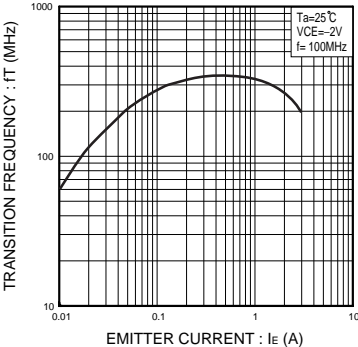


Fig.11 Gain bandwidth product vs. emitter current

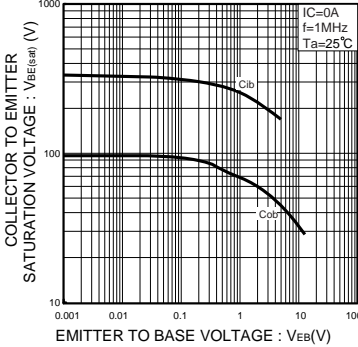


Fig.12 Collector output capacitance vs. collector-base voltage
Emitter input capacitance vs. emitter-base voltage

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